

SOT-89-3L Plastic-Encapsulate Transistors

A92 TRANSISTOR (PNP)

FEATURES

- Low Collector-Emitter Saturation Voltage
- High Breakdown Voltage

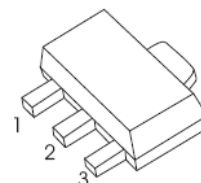
MARKING: A92

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-310	V
V _{CEO}	Collector-Emitter Voltage	-305	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current- Continuous	-200	mA
I _{CA}	Collector Current -Pulsed	-500	mA
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-310			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-305			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-200V, I _E =0			-0.25	μA
	I _{CEO}	V _{CE} =-200V, I _B =0			-0.25	μA
		V _{CE} =-300V, I _B =0			-5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C =-1mA	60			
	h _{FE(2)}	V _{CE} =-10V, I _C =-10mA	100		300	
	h _{FE(3)}	V _{CE} =-10V, I _C =-80mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B =-2mA			-0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-20mA, I _B =-2mA			-0.9	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=30MHz	50			MHz